

L Number	Hits	Search Text	DB	Time stamp
1	39	(electrode\$1 conduct\$3) near2 (free\$2 random\$2) near2 (arrang\$3 mov\$6) near2 (insulat\$3 dielectric substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 09:54
2	332	(phase near change) with (Ge near Sb near Te)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 09:54
3	46	((phase near change) with (Ge near Sb near Te)) and (electrode conduct\$3) with (Rh Pt Pd Ni Co Cr Re Ir Au)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:16
4	30	((((phase near change) with (Ge near Sb near Te)) and (electrode conduct\$3) with (Rh Pt Pd Ni Co Cr Re Ir Au)) and (polycarbonate near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17
5	166992	(electrode conduct\$3 contact),with (Rh Pt Pd Ni Co Cr Re Ir Au)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17
6	54	((electrode conduct\$3 contact) with (Rh Pt Pd Ni Co Cr Re Ir Au)) and ((phase near change) with (Ge near Sb near Te))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17
7	33	((((electrode conduct\$3 contact) with (Rh Pt Pd Ni Co Cr Re Ir Au)) and ((phase near change) with (Ge near Sb near Te))) and (polycarbonate near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17

L Number	Hits	Search Text	DB	Time stamp
1	3089644	non nearvolatile near memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:29
2	57541	non near volatile near memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:30
3	6674	cell\$1 with different with (electrode\$1 conductor\$1 contact\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:37
4	14	(cell\$1 with different with (electrode\$1 conductor\$1 contact\$1)) and (phase near charge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:34
5	99	(cell\$1 with different with (electrode\$1 conductor\$1 contact\$1)) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:50
6	273	(cell\$1 with different with (electrode\$1 conductor\$1 contact\$1)) and (non near volatile near memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:50
7	2	((cell\$1 with different with (electrode\$1 conductor\$1 contact\$1)) and (non near volatile near memory)) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:37
8	3	cell\$1 with different with (electrode\$1 conductor\$1 contact\$1) with (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:53
9	0	(memory near cell\$1) with different with (electrode\$1 conductor\$1 contact\$1) with (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:54
10	13	(memory near cell\$1) same different same (electrode\$1 conductor\$1 contact\$1) same (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:57
11	15	electrode\$1 with (randomly near (arrang\$3 configur\$3)) with (insulat\$3 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:13
12	41	electrode\$1 with (randomly near (arrang\$3 configur\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:21

13	41	electrode\$1 with (randomly near (arrang\$10 configur\$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:22
14	57	(non near volatile near memory) and (randomly near (arrang\$10 configur\$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:28
15	41	(advantage benefit\$1) with (randomly near (arrang\$10 configur\$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:35
16	443	(advantage benefit\$1) with random\$4 with (arrang\$10 configur\$10)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:36
17	43	(advantage benefit\$1) with (randomly near (arrang\$10 configur\$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:35
18	469	(advantage benefit\$1) with random\$4 with (arrang\$10 configur\$10)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:36
20	2	((advantage benefit\$1) with random\$4 with (arrang\$10 configur\$10)) and (electrode\$1 conductor\$1 contact\$1)) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:40
19	164	((advantage benefit\$1) with random\$4 with (arrang\$10 configur\$10)) and (electrode\$1 conductor\$1 contact\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:21
21	66	(electrode\$1 conductor\$1 contact\$1) near2 diameter near2 nm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:35
22	6	(electrode\$1 conductor\$1) near2 diameter near2 ((5.0 near nm) ("500" near nm)).	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:40
23	22777	(electrode\$1 conductor\$1) near2 diameter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:40
24	357	((electrode\$1 conductor\$1) near2 diameter) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:41

25	51	(((electrode\$1 conductor\$1) near2 diameter) and (phase near change)) and (non near volatile near memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:41
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